HE UNITED STATES PATENT AND TRADEMARK OFFICE

e the apple ation of: Y. INOUE et al.

PATENT APPLICATION

Serial No.: 08/921,250

Art Unit: 1763

Filed: August 29, 1997

Examiner: G. Goudreau

FABRICATION METHOD OF SEMICONDUCTOR DEVICE AND # 181) For:

ABRASIVE LIQUID USED THEREIN

AMENDMENT

Commissioner for Patents Washington, D.C. 20231

December 5, 2001

Sir:

In response to the Office Action dated September 6, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

E CLAIMS:

Please cancel claims 21 and 32 without prejudice or disclaimer.

Please cancel claims 21 and 32 without prejudice or disclaimer.

Please amend claims 3-5, 8-11, 13, 19 and 26 as follows:

2. (Three Times Amended) The fabrication method of a semiconductor device according to claim & wherein said step of planarization comprises the step of effecting planarization by polishing said first and second insulation films.